

*FIG. 1*

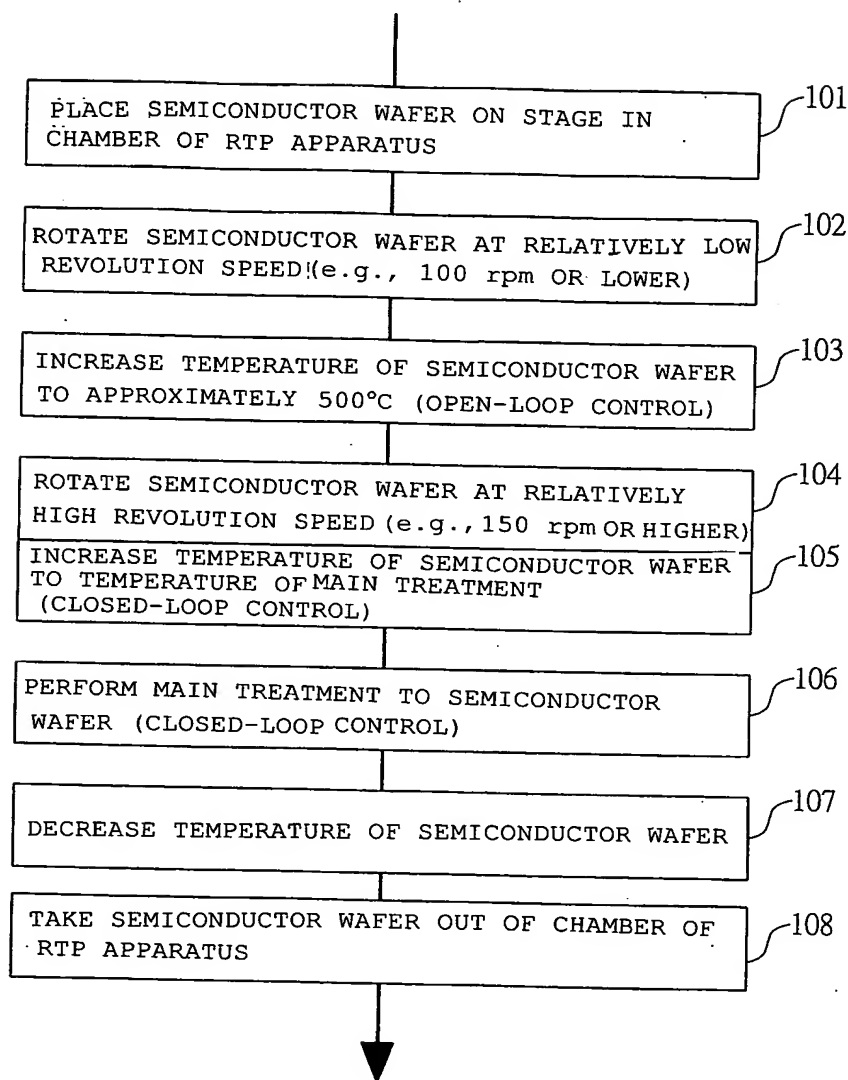
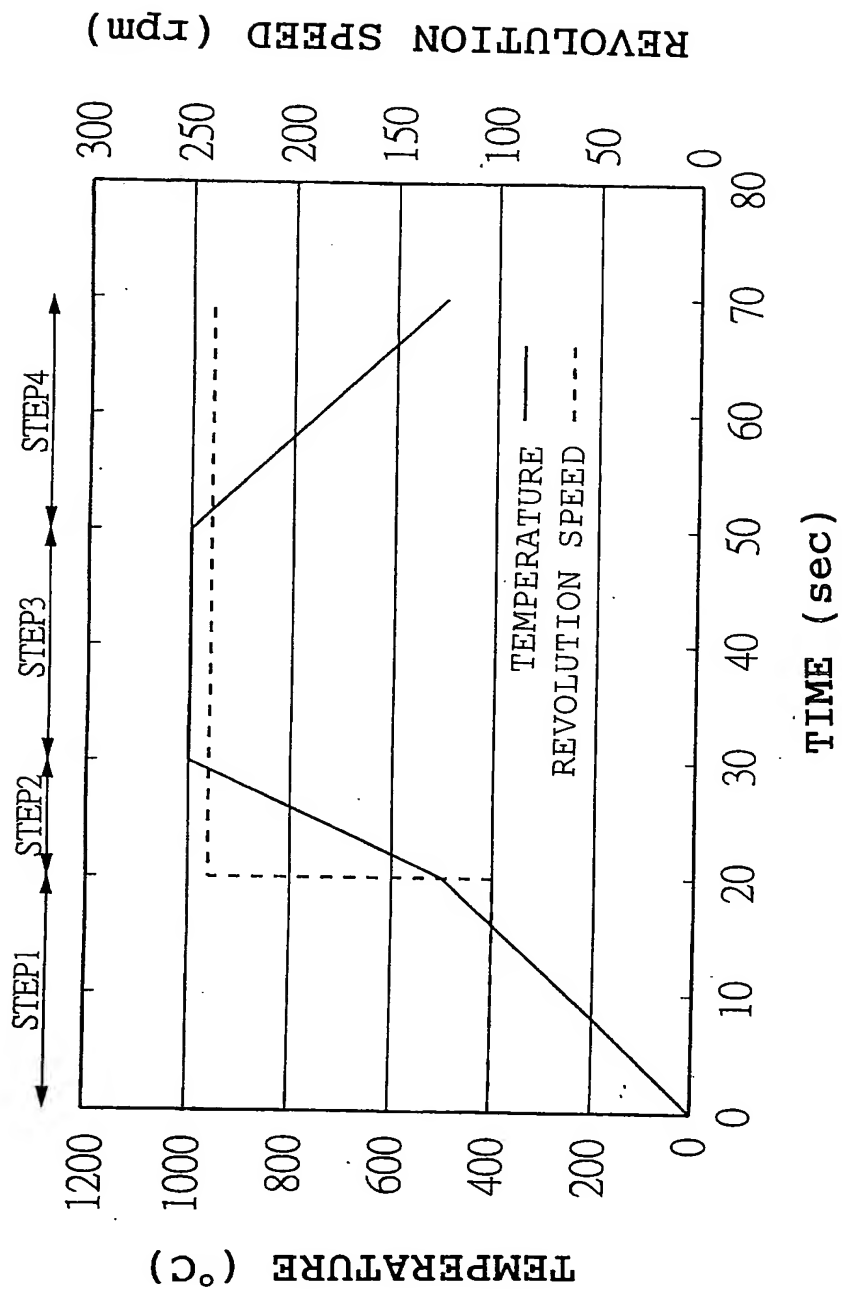


FIG. 2



### FIG. 3

FIG. 3A START ROTATION OF SEMICONDUCTOR  
WAFER

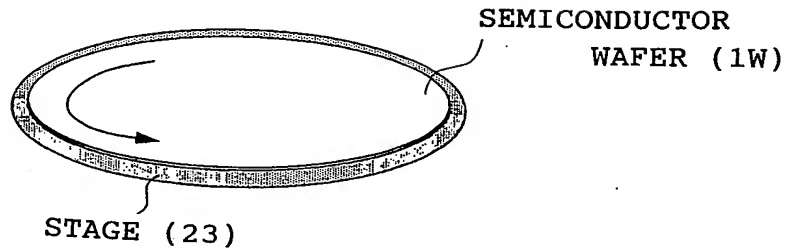


FIG. 3B

TEMPERATURE RISING PROCESS AT 500°C OR LOWER  
(NONUNIFORM IN-PLANE TEMPERATURE OF SEMICONDUCTOR WAFER)

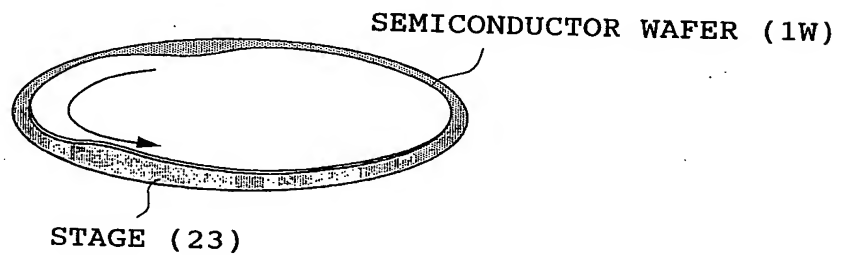


FIG. 3C

TEMPERATURE RISING PROCESS ABOVE 500°C AND MAIN  
TREATMENT PROCESS (UNIFORM IN-PLANE TEMPERATURE OF  
SEMICONDUCTOR WAFER)

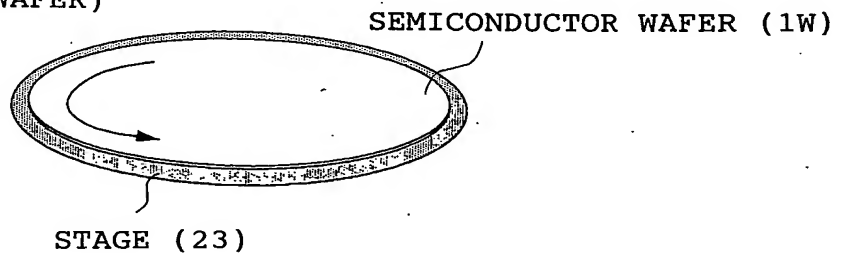


Fig. 1 is a perspective view of a multi-layered, elongated component. It features a central core (1) with diagonal hatching, flanked by layers (3) and (4). The top surface has a series of rectangular protrusions (2) and recessions (5).

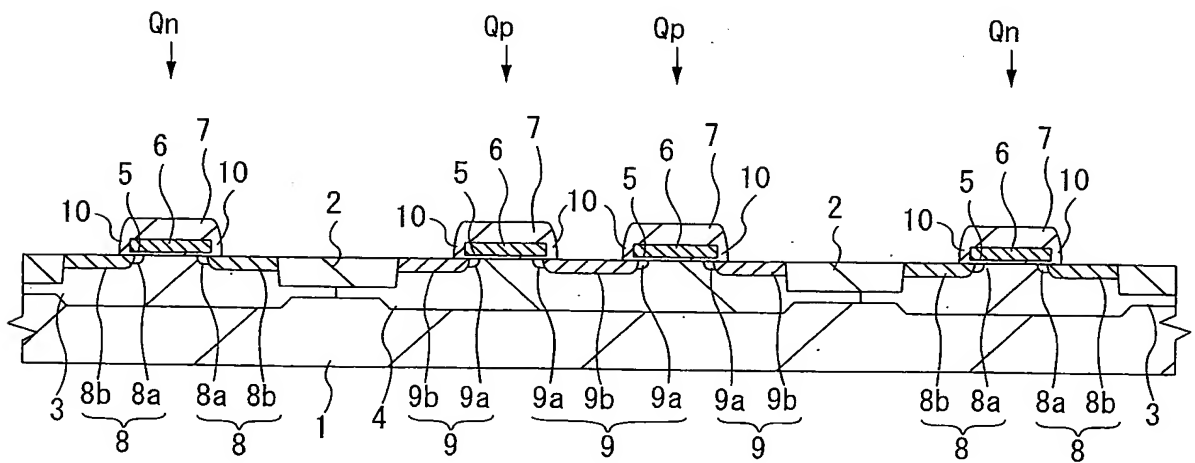


FIG. 6

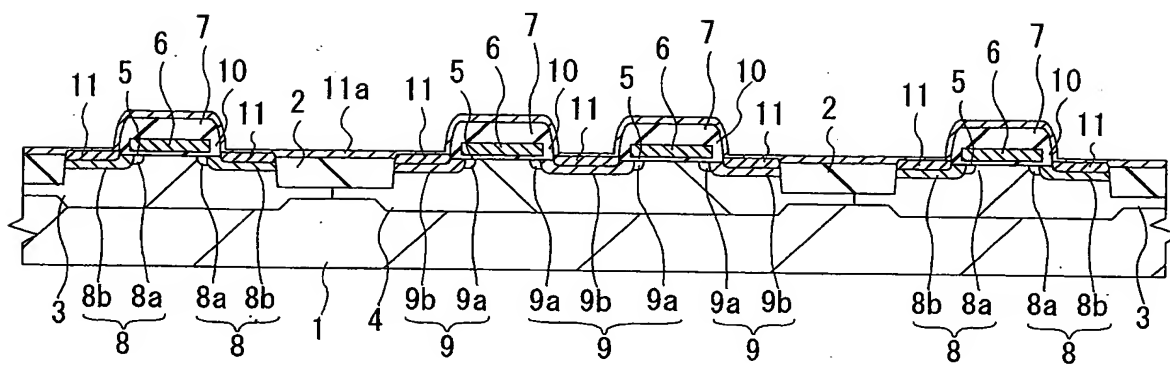


FIG. 7

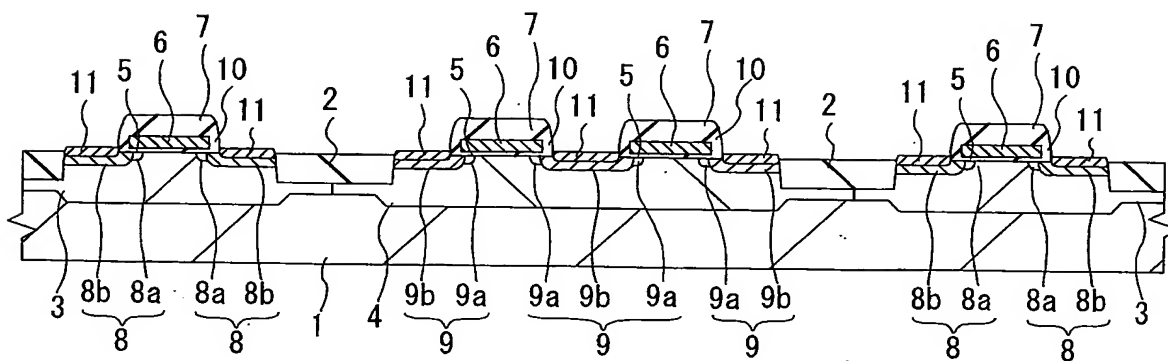
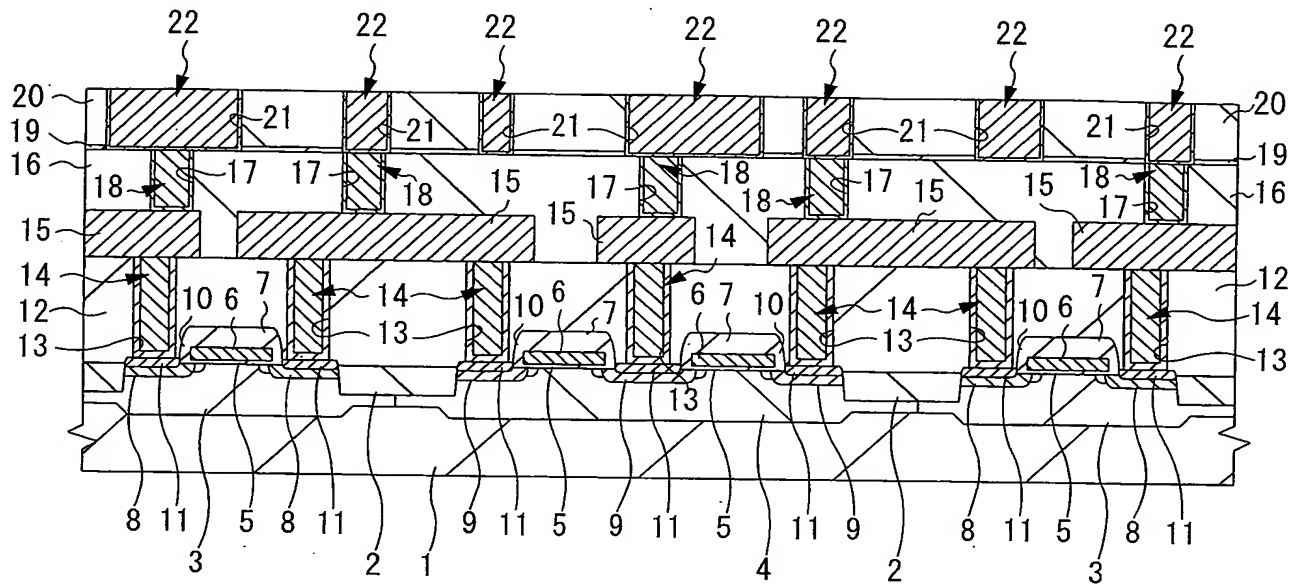


FIG. 8



*FIG. 9*

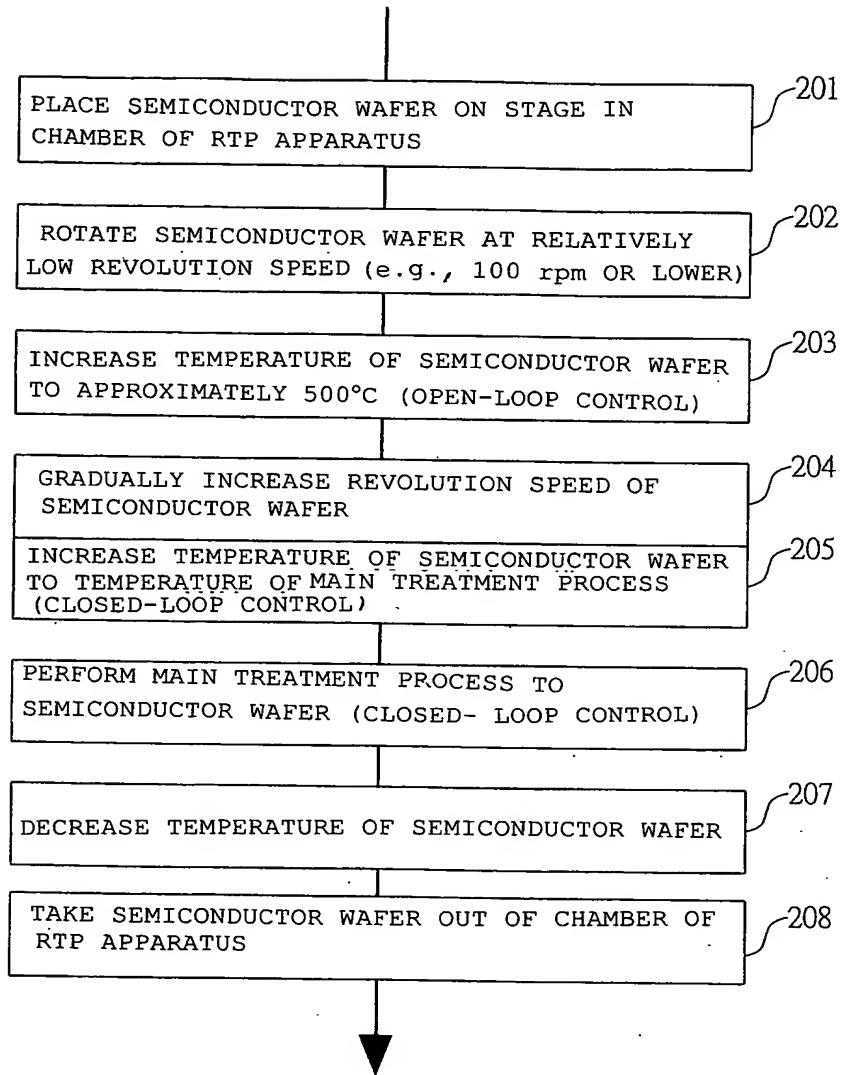
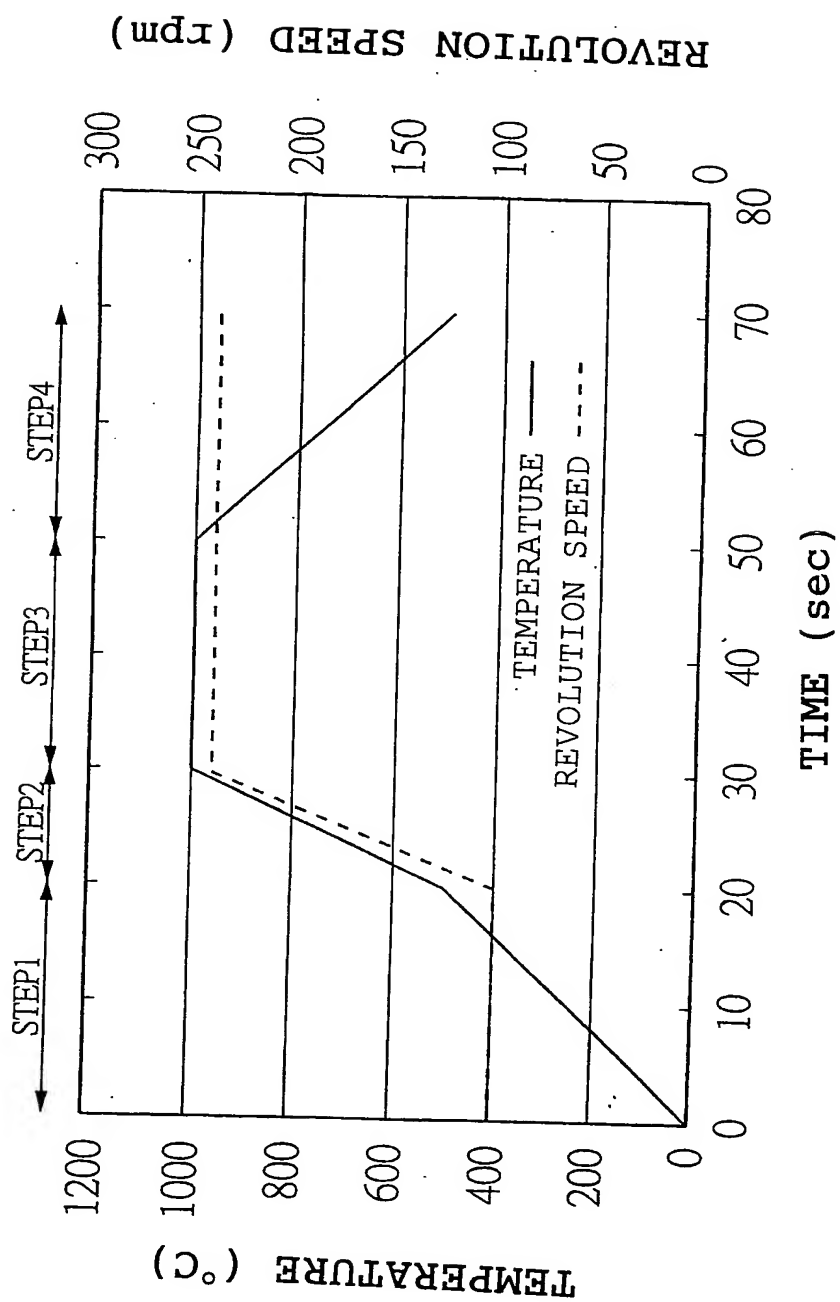


FIG. 10





*FIG. 11*

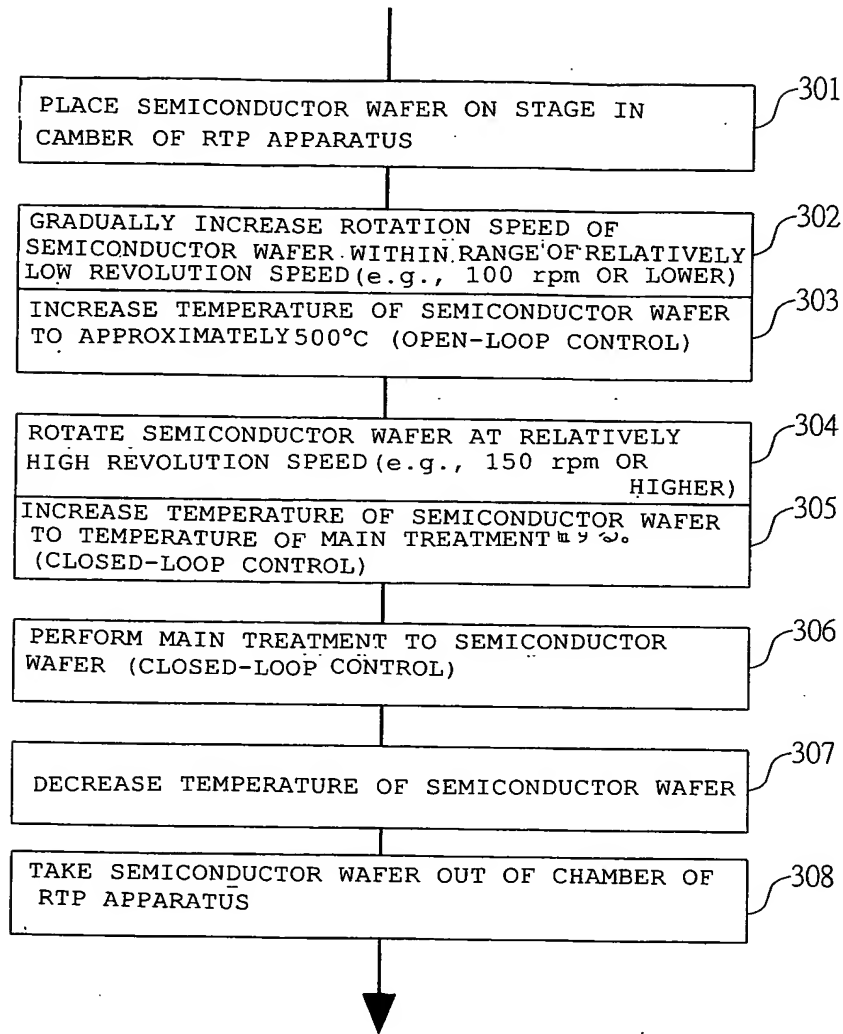


FIG. 12

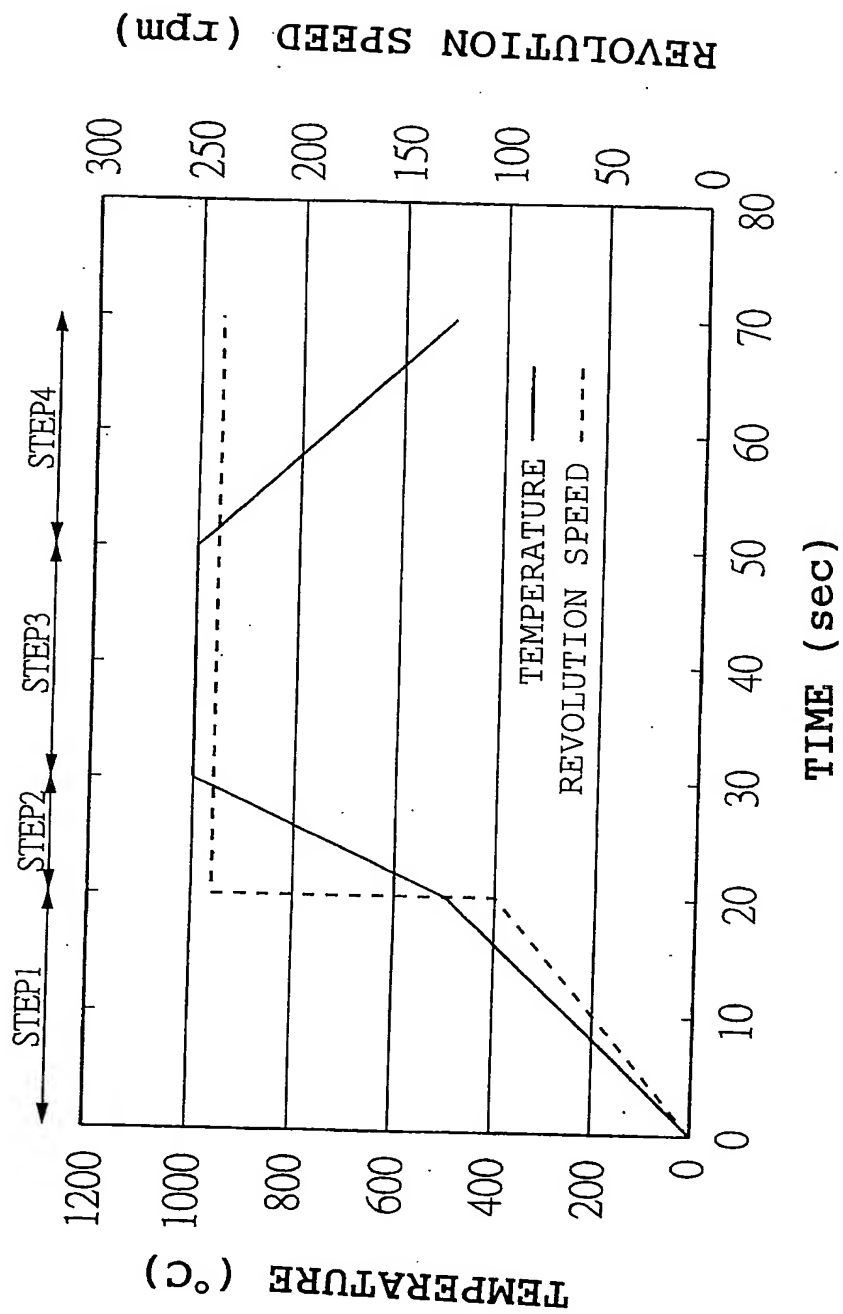


FIG. 13

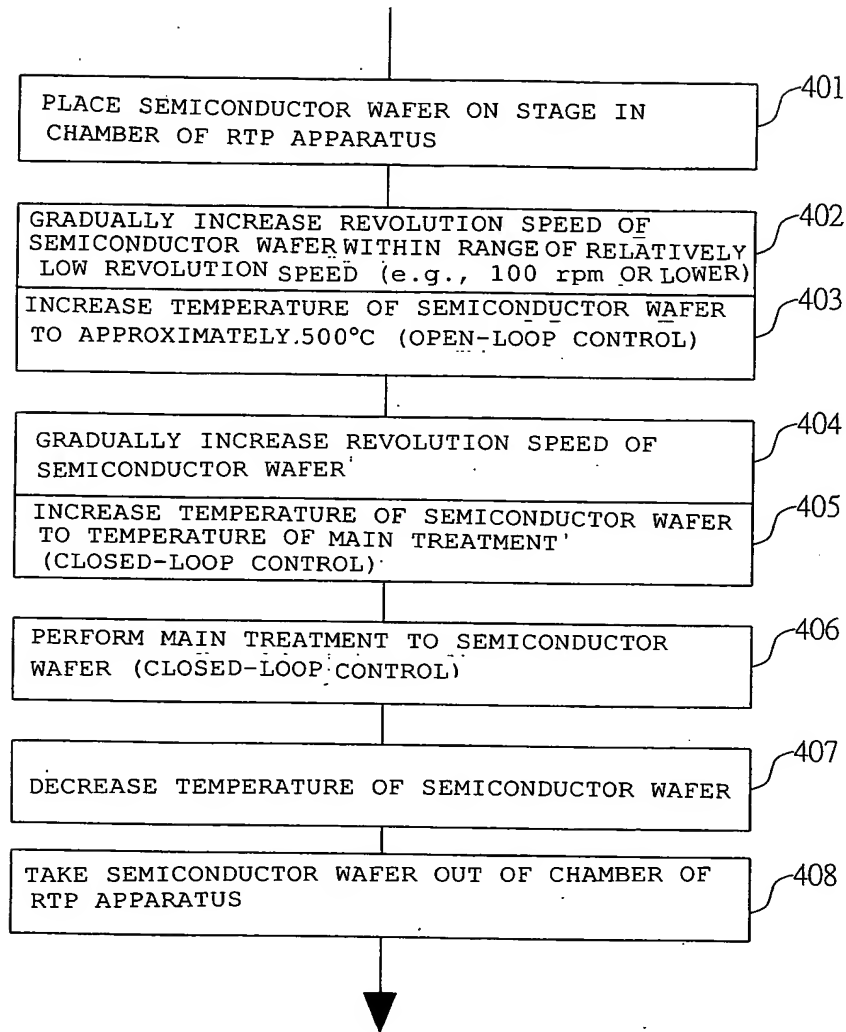


FIG. 14

